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August 2016

# FDMC89521L

## Dual N-Channel PowerTrench® MOSFET

### 60 V, 8.2 A, 17 mΩ

## Features

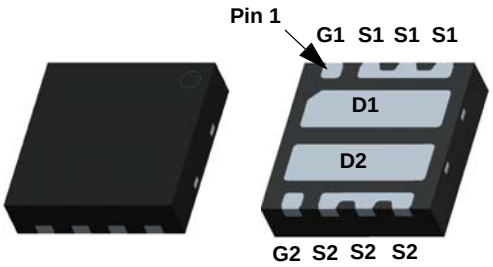
- Max $r_{DS(on)}$ = 17 mΩ at $V_{GS}$ = 10 V, $I_D$ = 8.2 A
- Max $r_{DS(on)}$ = 27 mΩ at $V_{GS}$ = 4.5 V, $I_D$ = 6.7 A
- Termination is Lead-free
- RoHS Compliant

## General Description

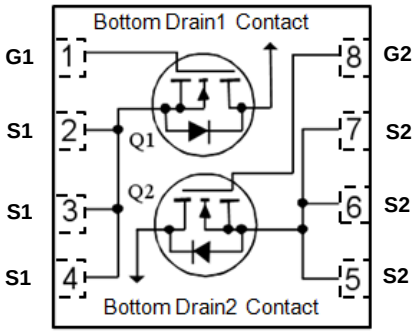
This device includes two 60 V N-Channel MOSFETs in a dual Power 33 (3 mm X 3 mm MLP) package. The package is enhanced for exceptional thermal performance.

## Applications

- Battery Protection
- Load Switching
- Bridge Topologies




Power 33




## MOSFET Maximum Ratings $T_A$ = 25 °C unless otherwise noted.

| Symbol | Parameter | | | Ratings | Units |
|---|---|---|---|---|---|
| $V_{DS}$ | Drain to Source Voltage | | | 60 | V |
| $V_{GS}$ | Gate to Source Voltage | | | ±20 | V |
| $I_D$ | Drain Current -Continuous | $T_A$ = 25 °C | (Note 1a) | 8.2 | A |
| | -Pulsed | | | 40 | |
| $E_{AS}$ | Single Pulse Avalanche Energy | | (Note 3) | 32 | mJ |
| $P_D$ | Power Dissipation | $T_C$ = 25 °C | | 16 | W |
| | Power Dissipation | $T_A$ = 25 °C | (Note 1a) | 1.9 | |
| $T_J$, $T_{STG}$ | Operating and Storage Junction Temperature Range | | | -55 to +150 | °C |

### Thermal Characteristics

| | | | | |
|---|---|---|---|---|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | | 8.0 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | (Note 1a) | 65 | |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | (Note 1b) | 155 | |

### Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|---|---|---|---|---|---|
| FDMC89521L | FDMC89521L | Power 33 | 13 ” | 12 mm | 3000 units |

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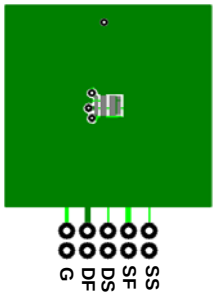
## Electrical Characteristics $T_J$ = 25 °C unless otherwise noted.

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|---|---|---|---|---|---|---|
| **Off Characteristics** | | | | | | |
| $BV_{DSS}$ | Drain to Source Breakdown Voltage | $I_D$ = 250 μA, $V_{GS}$ = 0 V | 60 | | | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D$ = 250 μA, referenced to 25 °C | | 30 | | mV/°C |
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{DS}$ = 48 V, $V_{GS}$ = 0 V | | | 1 | μA |
| $I_{GSS}$ | Gate to Source Leakage Current | $V_{GS}$ = ±20 V, $V_{DS}$ = 0 V | | | ±100 | nA |
| **On Characteristics** | | | | | | |
| $V_{GS(th)}$ | Gate to Source Threshold Voltage | $V_{GS}$ = $V_{DS}$, $I_D$ = 250 μA | 1 | 1.9 | 3 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate to Source Threshold Voltage Temperature Coefficient | $I_D$ = 250 μA, referenced to 25 °C | | -6 | | mV/°C |
| $r_{DS(on)}$ | Static Drain to Source On Resistance | $V_{GS}$ = 10 V, $I_D$ = 8.2 A | | 13 | 17 | mΩ |
| | | $V_{GS}$ = 4.5 V, $I_D$ = 6.7 A | | 21 | 27 | |
| | | $V_{GS}$ = 10 V, $I_D$ = 8.2 A, $T_J$ = 125 °C | | 20 | 26 | |
| $g_{FS}$ | Forward Transconductance | $V_{DS}$ = 10 V, $I_D$ = 8.2 A | | 28 | | S |
| **Dynamic Characteristics** | | | | | | |
| $C_{iss}$ | Input Capacitance | $V_{DS}$ = 30 V, $V_{GS}$ = 0 V, f = 1 MHz | | 1228 | 1635 | pF |
| $C_{oss}$ | Output Capacitance | | | 243 | 325 | pF |
| $C_{rss}$ | Reverse Transfer Capacitance | | | 10 | 15 | pF |
| $R_g$ | Gate Resistance | | | 0.7 | | Ω |
| **Switching Characteristics** | | | | | | |
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD}$ = 30 V, $I_D$ = 8.2 A, $V_{GS}$ = 10 V, $R_{GEN}$ = 6 Ω | | 7.9 | 16 | ns |
| $t_r$ | Rise Time | | | 2.1 | 10 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | | 18 | 33 | ns |
| $t_f$ | Fall Time | | | 1.7 | 10 | ns |
| $Q_g$ | Total Gate Charge | $V_{GS}$ = 0 V to 10 V; $V_{DD}$ = 30 V, $I_D$ = 8.2 A | | 17 | 24 | nC |
| $Q_g$ | Total Gate Charge | $V_{GS}$ = 0 V to 4.5 V; $V_{DD}$ = 30 V, $I_D$ = 8.2 A | | 7.9 | 12 | nC |
| $Q_{gs}$ | Gate to Source Charge | $V_{DD}$ = 30 V, $I_D$ = 8.2 A | | 3.8 | | nC |
| $Q_{gd}$ | Gate to Drain “Miller” Charge | $V_{DD}$ = 30 V, $I_D$ = 8.2 A | | 1.9 | | nC |
| **Drain-Source Diode Characteristics** | | | | | | |
| $V_{SD}$ | Source-Drain Diode Forward Voltage | $V_{GS}$ = 0 V, $I_S$ = 8.2 A (Note 2) | | 0.85 | 1.3 | V |
| | | $V_{GS}$ = 0 V, $I_S$ = 1.6 A (Note 2) | | 0.75 | 1.2 | |
| $t_{rr}$ | Reverse Recovery Time | $I_F$ = 8.2 A, di/dt = 100 A/μs | | 25 | 40 | ns |
| $Q_{rr}$ | Reverse Recovery Charge | | | 11 | 20 | nC |

Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 $in^2$ pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.




a. 65 °C/W when mounted on a 1 $in^2$ pad of 2 oz copper




b. 155 °C/W when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.

3. $E_{AS}$ of 32 mJ is based on starting $T_J$ = 25 °C, L = 1 mH, $I_{AS}$ = 8 A, $V_{DD}$ = 54 V, $V_{GS}$ = 10 V. 100% tested at L = 3 mH, $I_{AS}$ = 5.4 A.

## Typical Characteristics $T_J$ = 25 °C unless otherwise noted.

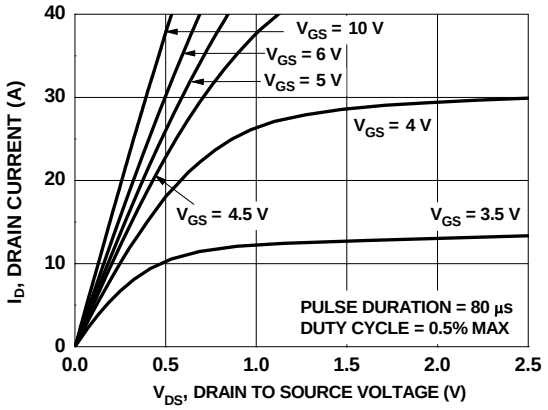



**Figure 1. On Region Characteristics**

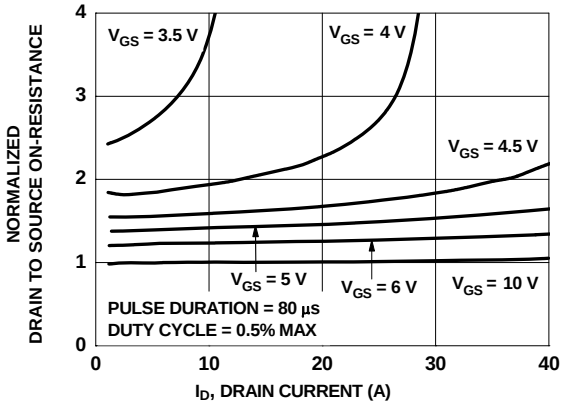



**Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage**

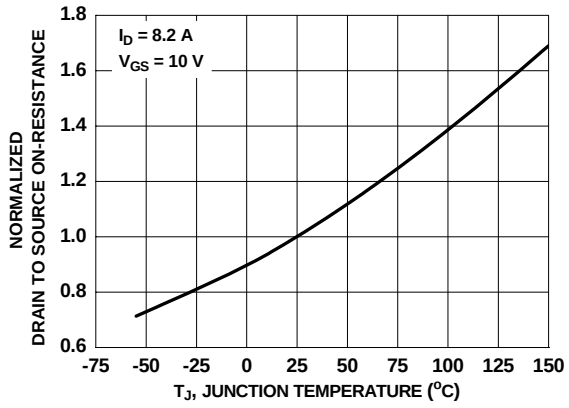



**Figure 3. Normalized On Resistance vs. Junction Temperature**

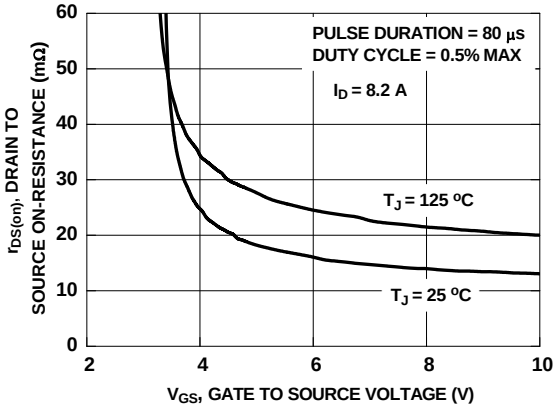



**Figure 4. On-Resistance vs. Gate to Source Voltage**

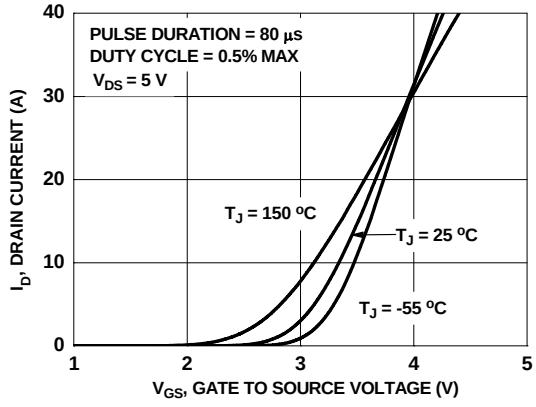



**Figure 5. Transfer Characteristics**

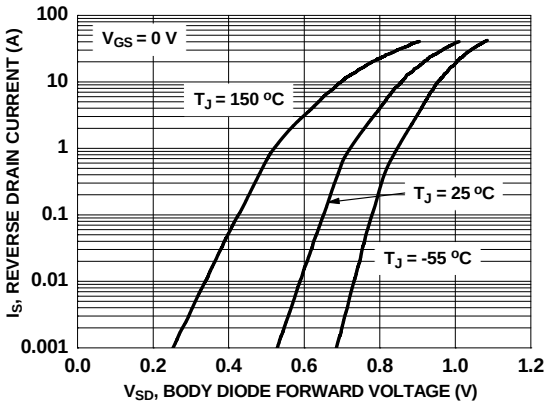



**Figure 6. Source to Drain Diode Forward Voltage vs. Source Current**

## Typical Characteristics $T_J$ = 25 °C unless otherwise noted.

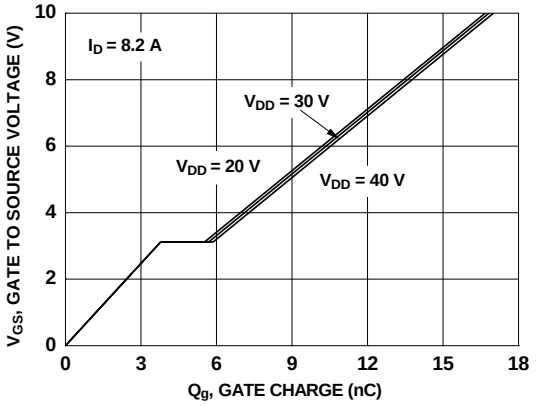



**Figure 7. Gate Charge Characteristics**

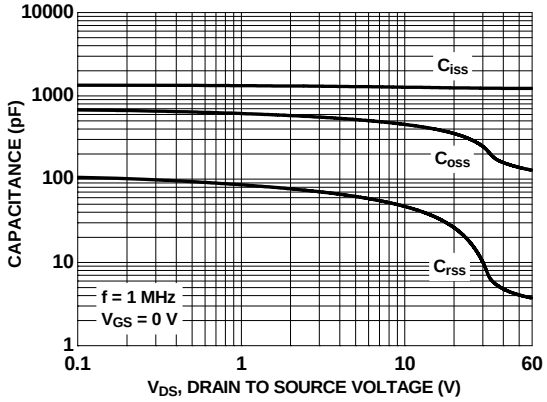



**Figure 8. Capacitance vs. Drain to Source Voltage**

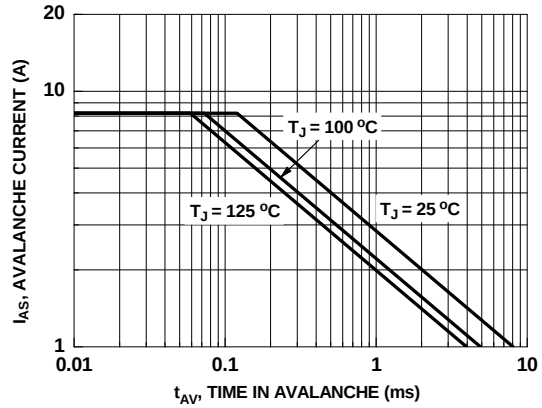



**Figure 9. Unclamped Inductive Switching Capability**

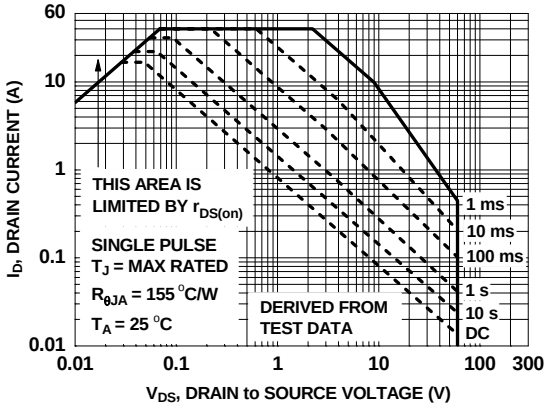



**Figure 10. Forward Bias Safe Operating Area**

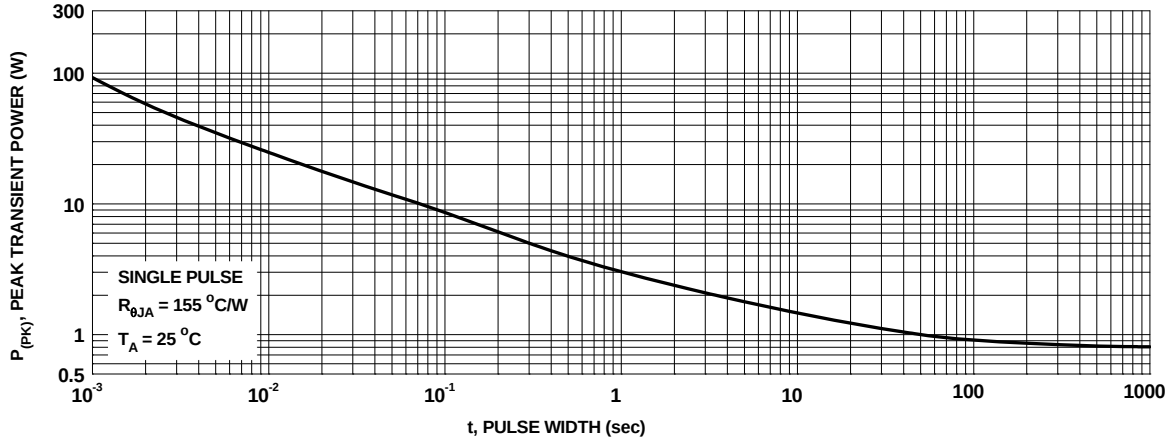



**Figure 11. Single Pulse Maximum Power Dissipation**

## Typical Characteristics $T_J$ = 25 °C unless otherwise noted.

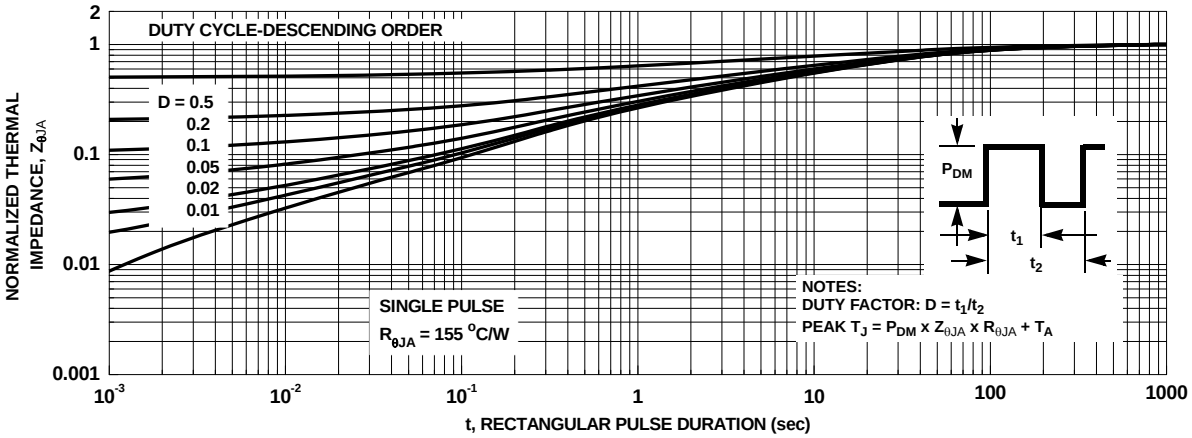
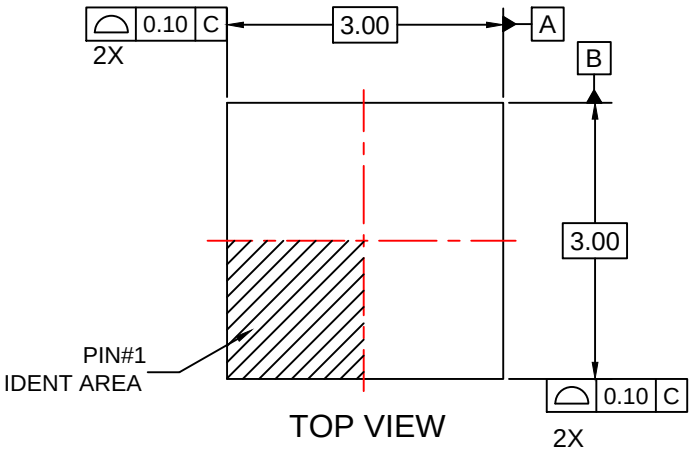
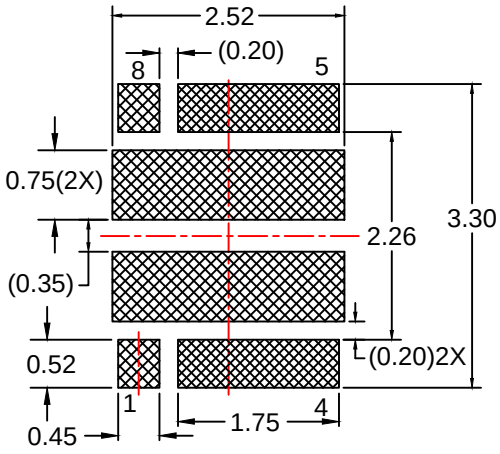



**Figure 12. Junction-to-Ambient Transient Thermal Response Curve**




TOP VIEW

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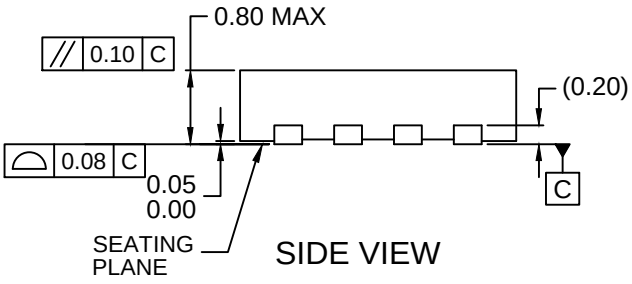


SIDE VIEW

NOTES:

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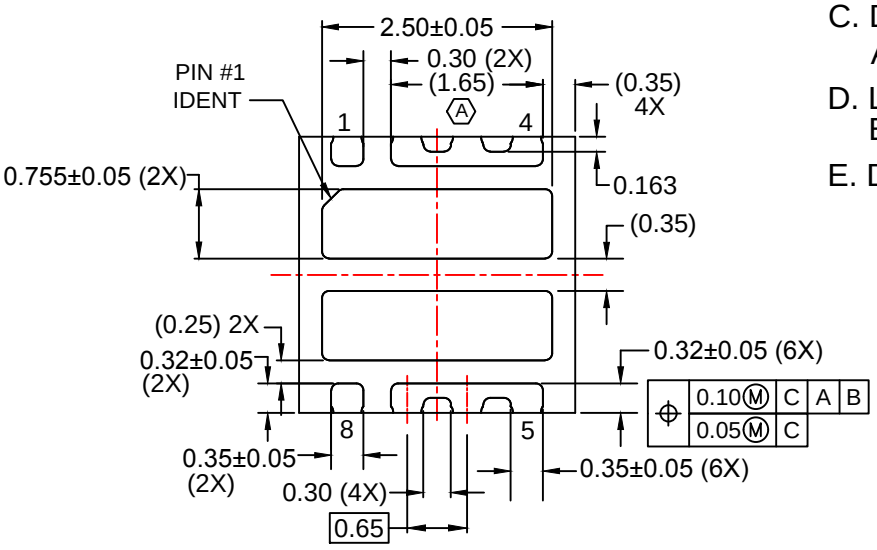


BOTTOM VIEW

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